

*P2*

- (c) heating said multilayer structure at a temperature less than 600°C to remove said first and second combinations of organic materials and their decomposition products, such as carbon, to levels below 200 ppm; thereafter
- (d) sintering at a temperature from about 600°C to about 1050°C at a partial pressure of oxygen from about  $10^{-3}$  to  $10^{-15}$  atm to produce said multilayer piezoelectric device with alternating piezoelectric ceramic layers and base metal layers as electrodes .

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*P3*

- 12. (Amended) The device of claim 10, wherein said base metal is selected from the group consisting of Cu, Ni and alloys thereof.
- 13. (Amended) The device of claim 10, wherein said first combination of organic materials includes binder, solvents, plasticizers, dispersants, and combinations thereof.
- 14. (Amended) The device of claim 10, wherein said second combination of organic materials includes solvents, binder, and combinations thereof.

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